



IRF7811WTRPBF Information



For Reference Only

Part Number IRF7811WTRPBF
Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

DescriptionMOSFET N-CH 30V 14A 8-SOIC**Package**8-SOIC (0.154", 3.90mm Width)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRF7811WTRPBF Specifications

Manufacturer Part Number IRF781WTRPBF Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-SOIC (0.154", 3.90mm Width) Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 14A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V Vgs(th) (Max) @ Id 1V @ 250µA Gate Charge (Qg) (Max) @ Vgs 33nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 2335pF @ 16V Vgs (Max) ±12V FET Feature - Power Dissipation (Max) 3.1W (Ta) Rds On (Max) @ Id, Vgs 12 mOhm @ 15A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)		
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C14A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs33nC @ 5VInput Capacitance (Ciss) (Max) @ Vds2335pF @ 16VVgs (Max)±12VFET Feature-Power Dissipation (Max)3.1W (Ta)Rds On (Max) @ Id, Vgs12 mOhm @ 15A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Package	8-SOIC (0.154", 3.90mm Width)
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C14A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs33nC @ 5VInput Capacitance (Ciss) (Max) @ Vds2335pF @ 16VVgs (Max)±12VFET Feature-Power Dissipation (Max)3.1W (Ta)Rds On (Max) @ Id, Vgs12 mOhm @ 15A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Series	HEXFET?
Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C14A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs33nC @ 5VInput Capacitance (Ciss) (Max) @ Vds2335pF @ 16VVgs (Max)±12VFET Feature-Power Dissipation (Max)3.1W (Ta)Rds On (Max) @ Id, Vgs12 mOhm @ 15A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C14A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs33nC @ 5VInput Capacitance (Ciss) (Max) @ Vds2335pF @ 16VVgs (Max)±12VFET Feature-Power Dissipation (Max)3.1W (Ta)Rds On (Max) @ Id, Vgs12 mOhm @ 15A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs33nC @ 5VInput Capacitance (Ciss) (Max) @ Vds2335pF @ 16VVgs (Max)±12VFET Feature-Power Dissipation (Max)3.1W (Ta)Rds On (Max) @ Id, Vgs12 mOhm @ 15A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 1V @ 250μA 13 nC @ 5V 2335pF @ 16V 235pF @ 16V 24pF @ 10PF @	Current - Continuous Drain (Id) @ 25°C	14A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 2335pF @ 16V Vgs (Max) ±12V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 12 mOhm @ 15A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Drive Voltage (Max Rds On, Min Rds On)	4.5V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 12 mOhm @ 15A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs(th) (Max) @ Id	1V @ 250μA
Vgs (Max)±12VFET Feature-Power Dissipation (Max)3.1W (Ta)Rds On (Max) @ Id, Vgs12 mOhm @ 15A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Gate Charge (Qg) (Max) @ Vgs	33nC @ 5V
FET Feature - Power Dissipation (Max) 3.1W (Ta) Rds On (Max) @ Id, Vgs 12 mOhm @ 15A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Input Capacitance (Ciss) (Max) @ Vds	2335pF @ 16V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 12 mOhm @ 15A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs (Max)	±12V
Rds On (Max) @ Id, Vgs12 mOhm @ 15A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Power Dissipation (Max)	3.1W (Ta)
Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Rds On (Max) @ Id, Vgs	12 mOhm @ 15A, 4.5V
Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 8-SOIC (0.154", 3.90mm Width)	Mounting Type	Surface Mount
	Supplier Device Package	8-SO
Report errors?	Package / Case	8-SOIC (0.154", 3.90mm Width)
		Report errors?

IRF7811WTRPBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRF7811WTRPBF Payment Methods



















IRF7811WTRPBF Shipping Methods













If you have any question about IRF7811WTRPBF, please do not hesitate to contact us!

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